

II. This is in response to the Office Action dated February 13, 2002, the period for reply having been extended by the above petition and payment of the extension fee. Please amend the above-identified application as follows and consider the following remarks.

IN THE CLAIMS:

Please cancel claims 7 and 8 without prejudice or disclaimer.

Please amend claims 1, 6 and 11-13 as follows. A marked-up copy of the claims, showing the changes made thereto, is attached.

1. (Amended) A deposited-film formation method comprising the steps of:

providing a discharge electrode in a vacuum vessel equipped with exhaust means;

supplying a hydrogen gas and a raw material gas for forming a deposited film which contains at least an Si element;

generating plasma from the material gas by supplying high frequency electric power of 1 MHz to 200 MHz to the discharge electrode; and

forming a deposited film on a substrate in the vacuum vessel by plasma CVD,

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wherein an auxiliary electrode is arranged in plasma in the vacuum vessel,  
and a periodically changing voltage having a frequency of 100 kHz to 5 GHz is applied to  
the auxiliary electrode without causing a discharge to form a deposited film while  
controlling generation of hydrogen radicals.

6. (Amended) The deposited-film formation method according to  
claim 1, wherein a plurality of auxiliary electrodes is arranged at least in a flow direction of  
the material gas.

10. (Amended) The deposited-film formation method according to  
claim 1, wherein the auxiliary electrode is formed from a round bar which has a small  
diameter and which is made of a high strength material of a high melting point metal.

11. (Amended) A deposited-film formation method comprising the steps  
of:  
means;  
providing a discharge electrode in a vacuum vessel equipped with exhaust  
supplying a hydrogen gas and a raw material gas for forming a deposited  
film which contains at least an Si element;  
generating plasma from the material gas by supplying high frequency  
electric power of 1 MHz to 200 MHz to the discharge electrode; and

forming a deposited film on a substrate in the vacuum vessel by plasma CVD,  
wherein an auxiliary electrode is arranged in plasma in the vacuum vessel, a periodically changing voltage having a frequency of 100 kHz to 5 GHz is applied to the auxiliary electrode so that a voltage lower than the potential of plasma from the material gas is applied only in a certain period in at least one cycle of the periodically changing voltage, thereby forming a deposited film and controlling generation of hydrogen radicals.

12. (Amended) A deposited-film formation method comprising the steps of:

providing a discharge electrode in a vacuum vessel equipped with exhaust means;

supplying a hydrogen gas and a raw material gas for forming a deposited film which contains at least an Si element;

generating plasma from the material gas by supplying high frequency electric power to the discharge electrode; and

forming a deposited film on a substrate in the vacuum vessel by plasma CVD,

wherein an auxiliary electrode is arranged in plasma in the vacuum vessel, a high-frequency power of 1 MHz to 200 MHz is applied to the discharge electrode, and a high-frequency power of 100 kHz to 5 MHz to the auxiliary electrode, thereby forming a deposited film and controlling generation of hydrogen radicals.